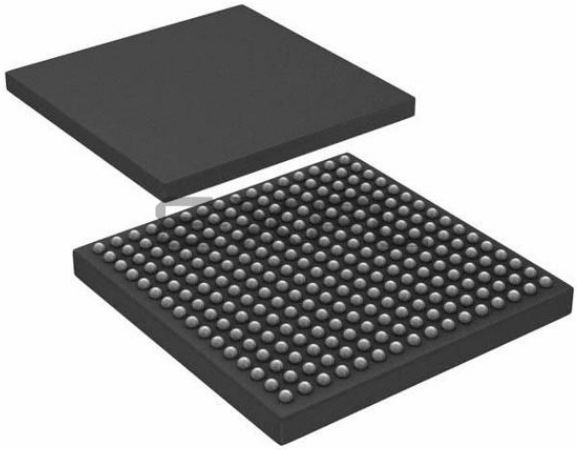


Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	13824
Total RAM Bits	110592
Number of I/O	177
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1agl600v2-fgg256i

IGLOO Device Family Overview

IGLOO DC and Switching Characteristics

Pin Descriptions

Package Pin Assignments

Datasheet Information

1 – IGLOO Device Family Overview

General Description

The IGLOO family of flash FPGAs, based on a 130-nm flash process, offers the lowest power FPGA, a single-chip solution, small footprint packages, reprogrammability, and an abundance of advanced features.

The Flash*Freeze technology used in IGLOO devices enables entering and exiting an ultra-low power mode that consumes as little as 5 µW while retaining SRAM and register data. Flash*Freeze technology simplifies power management through I/O and clock management with rapid recovery to operation mode.

The Low Power Active capability (static idle) allows for ultra-low power consumption (from 12 µW) while the IGLOO device is completely functional in the system. This allows the IGLOO device to control system power management based on external inputs (e.g., scanning for keyboard stimulus) while consuming minimal power.

Nonvolatile flash technology gives IGLOO devices the advantage of being a secure, low power, single-chip solution that is Instant On. IGLOO is reprogrammable and offers time-to-market benefits at an ASIC-level unit cost.

These features enable designers to create high-density systems using existing ASIC or FPGA design flows and tools.

IGLOO devices offer 1 kbit of on-chip, reprogrammable, nonvolatile FlashROM storage as well as clock conditioning circuitry based on an integrated phase-locked loop (PLL). The AGL015 and AGL030 devices have no PLL or RAM support. IGLOO devices have up to 1 million system gates, supported with up to 144 kbits of true dual-port SRAM and up to 300 user I/Os.

M1 IGLOO devices support the high-performance, 32-bit Cortex-M1 processor developed by ARM for implementation in FPGAs. Cortex-M1 is a soft processor that is fully implemented in the FPGA fabric. It has a three-stage pipeline that offers a good balance between low power consumption and speed when implemented in an M1 IGLOO device. The processor runs the ARMv6-M instruction set, has a configurable nested interrupt controller, and can be implemented with or without the debug block. Cortex-M1 is available for free from Microsemi for use in M1 IGLOO FPGAs.

The ARM-enabled devices have ordering numbers that begin with M1AGL and do not support AES decryption.

Flash*Freeze Technology

The IGLOO device offers unique Flash*Freeze technology, allowing the device to enter and exit ultra-low power Flash*Freeze mode. IGLOO devices do not need additional components to turn off I/Os or clocks while retaining the design information, SRAM content, and registers. Flash*Freeze technology is combined with in-system programmability, which enables users to quickly and easily upgrade and update their designs in the final stages of manufacturing or in the field. The ability of IGLOO V2 devices to support a wide range of core voltage (1.2 V to 1.5 V) allows further reduction in power consumption, thus achieving the lowest total system power.

When the IGLOO device enters Flash*Freeze mode, the device automatically shuts off the clocks and inputs to the FPGA core; when the device exits Flash*Freeze mode, all activity resumes and data is retained.

The availability of low power modes, combined with reprogrammability, a single-chip and single-voltage solution, and availability of small-footprint, high pin-count packages, make IGLOO devices the best fit for portable electronics.

- Wide input frequency range (f_{IN_CCC}) = 1.5 MHz up to 250 MHz
- Output frequency range (f_{OUT_CCC}) = 0.75 MHz up to 250 MHz
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis (for PLL only)

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration (for PLL only).
- Output duty cycle = 50% ± 1.5% or better (for PLL only)
- Low output jitter: worst case < 2.5% × clock period peak-to-peak period jitter when single global network used (for PLL only)
- Maximum acquisition time is 300 µs (for PLL only)
- Exceptional tolerance to input period jitter—allowable input jitter is up to 1.5 ns (for PLL only)
- Four precise phases; maximum misalignment between adjacent phases of 40 ps × 250 MHz / f_{OUT_CCC} (for PLL only)

Global Clocking

IGLOO devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high-fanout nets.

I/Os with Advanced I/O Standards

The IGLOO family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.0 V wide range, and 3.3 V). IGLOO FPGAs support many different I/O standards—single-ended and differential.

The I/Os are organized into banks, with two or four banks per device. The configuration of these banks determines the I/O standards supported (Table 1-1).

Table 1-1 • **I/O Standards Supported**

I/O Bank Type	Device and Bank Location	I/O Standards Supported		
		LVTTL/ LVCMOS	PCI/PCI-X	LVPECL, LVDS, B-LVDS, M-LVDS
Advanced	East and west banks of AGL250 and larger devices	✓	✓	✓
Standard Plus	North and south banks of AGL250 and larger devices All banks of AGL060 and AGL125K	✓	✓	Not supported
Standard	All banks of AGL015 and AGL030	✓	Not supported	Not supported

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following:

- Single-Data-Rate applications
- Double-Data-Rate applications—DDR LVDS, B-LVDS, and M-LVDS I/Os for point-to-point communications

IGLOO banks for the AGL250 device and above support LVPECL, LVDS, B-LVDS, and M-LVDS. B-LVDS and M-LVDS can support up to 20 loads.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Package Thermal Characteristics

The device junction-to-case thermal resistivity is θ_{jc} and the junction-to-ambient air thermal resistivity is θ_{ja}. The thermal characteristics for θ_{ja} are shown for two air flow rates. The absolute maximum junction temperature is 100°C. EQ 2 shows a sample calculation of the absolute maximum power dissipation allowed for the AGL1000-FG484 package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. (°C)} - \text{Max. ambient temp. (°C)}}{\theta_{ja}(\text{°C/W})} = \frac{100\text{°C} - 70\text{°C}}{23.3\text{°C/W}} = 1.28\ \text{W}$$

EQ 2

Table 2-5 • **Package Thermal Resistivities**

Package Type	Device	Pin Count	θ_{jc}	θ_{ja}			Unit
				Still Air	1 m/s	2.5 m/s	
Quad Flat No Lead (QN)	AGL030	132	13.1	21.4	16.8	15.3	C/W
	AGL060	132	11.0	21.2	16.6	15.0	C/W
	AGL125	132	9.2	21.1	16.5	14.9	C/W
	AGL250	132	8.9	21.0	16.4	14.8	C/W
	AGL030	68	13.4	68.4	45.8	43.1	C/W
Very Thin Quad Flat Pack (VQ)*		100	10.0	35.3	29.4	27.1	C/W
Chip Scale Package (CS)	AGL1000	281	6.0	28.0	22.8	21.5	C/W
	AGL400	196	7.2	37.1	31.1	28.9	C/W
	AGL250	196	7.6	38.3	32.2	30.0	C/W
	AGL125	196	8.0	39.5	33.4	31.1	C/W
	AGL030	81	12.4	32.8	28.5	27.2	C/W
	AGL060	81	11.1	28.8	24.8	23.5	C/W
	AGL250	81	10.4	26.9	22.3	20.9	C/W
Micro Chip Scale Package (UC)	AGL030	81	16.9	40.6	35.2	33.7	C/W
Fine Pitch Ball Grid Array (FG)	AGL060	144	18.6	55.2	49.4	47.2	C/W
	AGL1000	144	6.3	31.6	26.2	24.2	C/W
	AGL400	144	6.8	37.6	31.2	29.0	C/W
	AGL250	256	12.0	38.6	34.7	33.0	C/W
	AGL1000	256	6.6	28.1	24.4	22.7	C/W
	AGL1000	484	8.0	23.3	19.0	16.7	C/W

*Note: *Thermal resistances for other device-package combinations will be posted in a later revision.*

Disclaimer:

The simulation for determining the junction-to-air thermal resistance is based on JEDEC standards (JESD51) and assumptions made in building the model. Junction-to-case is based on SEMI G38-88. JESD51 is only used for comparing one package to another package, provided the two tests uses the same condition. They have little relevance in actual application and therefore should be used with a degree of caution.

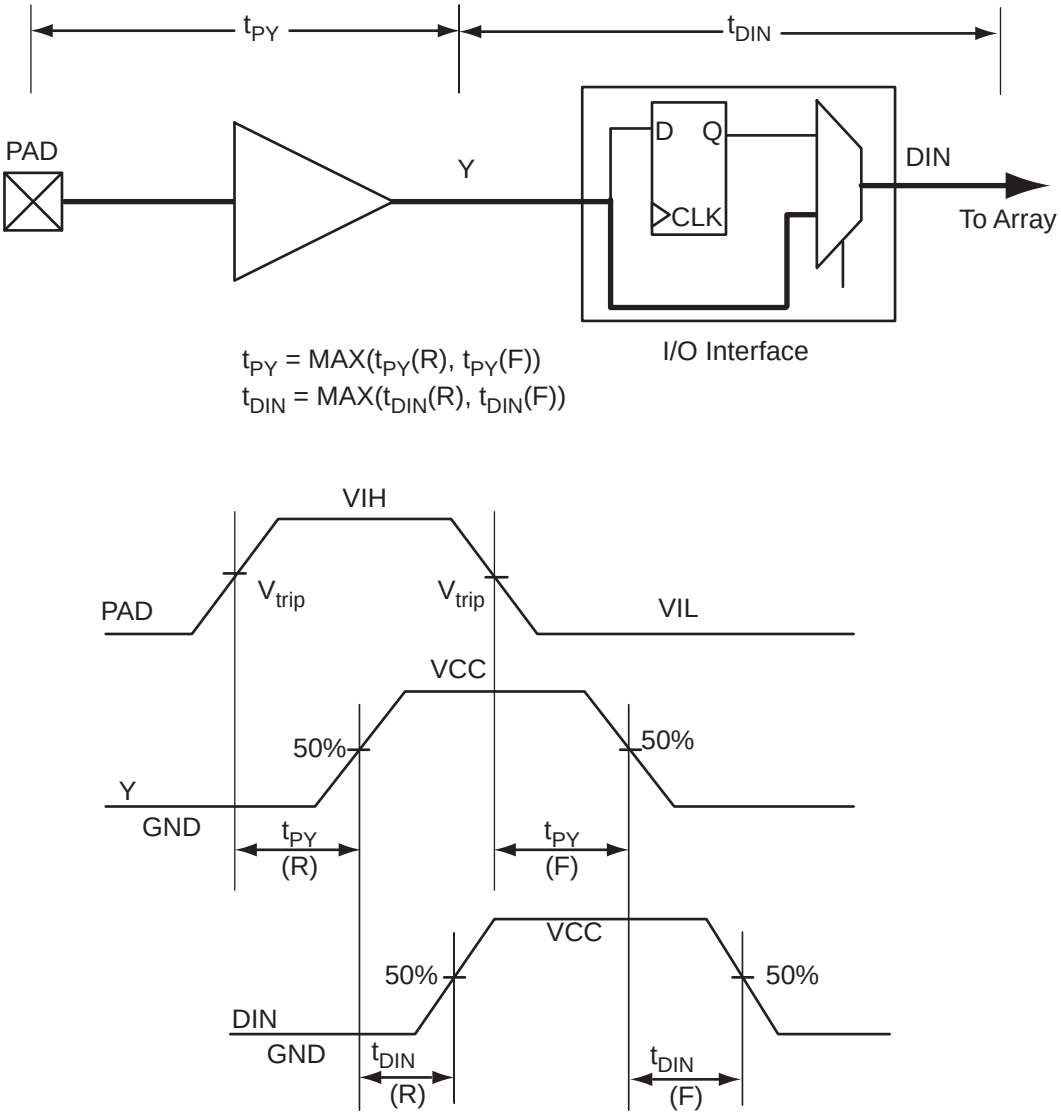


Figure 2-4 • **Input Buffer Timing Model and Delays (example)**

Table 2-31 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI (per standard) Applicable to Advanced I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1] (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12	High	5	–	0.97	2.09	0.18	0.85	0.66	2.14	1.68	2.67	3.05	5.73	5.27	ns
3.3 V LVCMOS Wide Range[2]	100 µA	12	High	5	–	0.97	2.93	0.18	1.19	0.66	2.95	2.27	3.81	4.30	6.54	5.87	ns
2.5 V LVCMOS	12 mA	12	High	5	–	0.97	2.09	0.18	1.08	0.66	2.14	1.83	2.73	2.93	5.73	5.43	ns
1.8 V LVCMOS	12 mA	12	High	5	–	0.97	2.24	0.18	1.01	0.66	2.29	2.00	3.02	3.40	5.88	5.60	ns
1.5 V LVCMOS	12 mA	12	High	5	–	0.97	2.50	0.18	1.17	0.66	2.56	2.27	3.21	3.48	6.15	5.86	ns
3.3 V PCI	Per PCI spec	–	High	10	25 [2]	0.97	2.32	0.18	0.74	0.66	2.37	1.78	2.67	3.05	5.96	5.38	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25 [2]	0.97	2.32	0.19	0.70	0.66	2.37	1.78	2.67	3.05	5.96	5.38	ns
LVDS	24 mA	–	High	–	–	0.97	1.74	0.19	1.35	–	–	–	–	–	–	–	ns
LVPECL	24 mA	–	High	–	–	0.97	1.68	0.19	1.16	–	–	–	–	–	–	–	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-12 on page 2-79 for connectivity. This resistor is not required during normal operation.*
4. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-33 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI (per standard) Applicable to Standard I/O Banks

I/O Standard	Drive Strength)	Equivalent Software Default Drive Strength Option[1] (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8	High	5	–	0.97	1.85	0.18	0.83	0.66	1.89	1.46	1.96	2.26	ns
3.3 V LVCMOS Wide Range[2]	100 µA	8	High	5	–	0.97	2.62	0.18	1.17	0.66	2.63	2.02	2.79	3.17	ns
2.5 V LVCMOS	8 mA	8	High	5	–	0.97	1.88	0.18	1.04	0.66	1.92	1.63	1.95	2.15	ns
1.8 V LVCMOS	4 mA	4	High	5	–	0.97	2.18	0.18	0.98	0.66	2.22	1.93	1.97	2.06	ns
1.5 V LVCMOS	2 mA	2	High	5	–	0.97	2.51	0.18	1.14	0.66	2.56	2.21	1.99	2.03	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-43 • I/O Short Currents IOSH/IOSL
Applicable to Standard Plus I/O Banks

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
	12 mA	103	109
	16 mA	103	109
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
	12 mA	65	74
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	35	44
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
1.2 V LVCMOS	2 mA	20	26
1.2 V LVCMOS Wide Range	100 µA	20	26
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	103	109

*Note: *T_J = 100°C*

Table 2-49 • Minimum and Maximum DC Input and Output Levels Applicable to Standard I/O Banks

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		V_{OL}	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

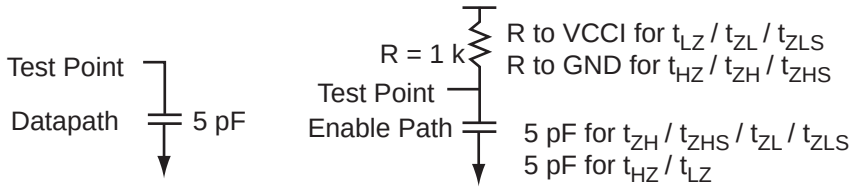


Figure 2-7 • AC Loading

Table 2-50 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	1.4	5

*Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.*

Applies to 1.2 V DC Core Voltage

Table 2-73 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7 V
Applicable to Advanced Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	2 mA	Std.	1.55	7.52	0.26	1.32	1.10	7.52	6.38	3.84	4.02	13.31	12.16	ns
100 µA	4 mA	Std.	1.55	7.52	0.26	1.32	1.10	7.52	6.38	3.84	4.02	13.31	12.16	ns
100 µA	6 mA	Std.	1.55	6.37	0.26	1.32	1.10	6.37	5.57	4.23	4.73	12.16	11.35	ns
100 µA	8 mA	Std.	1.55	6.37	0.26	1.32	1.10	6.37	5.57	4.23	4.73	12.16	11.35	ns
100 µA	12 mA	Std.	1.55	5.55	0.26	1.32	1.10	5.55	4.96	4.50	5.18	11.34	10.75	ns
100 µA	16 mA	Std.	1.55	5.32	0.26	1.32	1.10	5.32	4.82	4.56	5.29	11.10	10.61	ns
100 µA	24 mA	Std.	1.55	5.19	0.26	1.32	1.10	5.19	4.85	4.63	5.74	10.98	10.63	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-74 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7
Applicable to Advanced Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	2 mA	Std.	1.55	4.75	0.26	1.32	1.10	4.75	3.77	3.84	4.27	10.54	9.56	ns
100 µA	4 mA	Std.	1.55	4.75	0.26	1.32	1.10	4.75	3.77	3.84	4.27	10.54	9.56	ns
100 µA	6 mA	Std.	1.55	4.10	0.26	1.32	1.10	4.10	3.19	4.24	4.98	9.88	8.98	ns
100 µA	8 mA	Std.	1.55	4.10	0.26	1.32	1.10	4.10	3.19	4.24	4.98	9.88	8.98	ns
100 µA	12 mA	Std.	1.55	3.73	0.26	1.32	1.10	3.73	2.91	4.51	5.43	9.52	8.69	ns
100 µA	16 mA	Std.	1.55	3.67	0.26	1.32	1.10	3.67	2.85	4.57	5.55	9.46	8.64	ns
100 µA	24 mA	Std.	1.55	3.70	0.26	1.32	1.10	3.70	2.79	4.65	6.01	9.49	8.58	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*
3. *Software default selection highlighted in gray.*

Timing Characteristics

1.5 V DC Core Voltage

Table 2-115 • 1.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	6.62	0.18	1.17	0.66	6.75	6.06	2.79	2.31	10.35	9.66	ns
4 mA	Std.	0.97	5.75	0.18	1.17	0.66	5.86	5.34	3.06	2.78	9.46	8.93	ns
6 mA	Std.	0.97	5.43	0.18	1.17	0.66	5.54	5.19	3.12	2.90	9.13	8.78	ns
8 mA	Std.	0.97	5.35	0.18	1.17	0.66	5.46	5.20	2.63	3.36	9.06	8.79	ns
12 mA	Std.	0.97	5.35	0.18	1.17	0.66	5.46	5.20	2.63	3.36	9.06	8.79	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-116 • 1.5 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.97	0.18	1.17	0.66	3.04	2.90	2.78	2.40	6.63	6.50	ns
4 mA	Std.	0.97	2.60	0.18	1.17	0.66	2.65	2.45	3.05	2.88	6.25	6.05	ns
6 mA	Std.	0.97	2.53	0.18	1.17	0.66	2.58	2.37	3.11	3.00	6.18	5.96	ns
8 mA	Std.	0.97	2.50	0.18	1.17	0.66	2.56	2.27	3.21	3.48	6.15	5.86	ns
12 mA	Std.	0.97	2.50	0.18	1.17	0.66	2.56	2.27	3.21	3.48	6.15	5.86	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-117 • 1.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	5.93	0.18	1.18	0.66	6.04	5.46	2.30	2.15	9.64	9.06	ns
4 mA	Std.	0.97	5.11	0.18	1.18	0.66	5.21	4.80	2.54	2.58	8.80	8.39	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-118 • 1.5 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.58	0.18	1.18	0.66	2.64	2.41	2.29	2.24	6.23	6.01	ns
4 mA	Std.	0.97	2.25	0.18	1.18	0.66	2.30	2.00	2.53	2.68	5.89	5.59	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

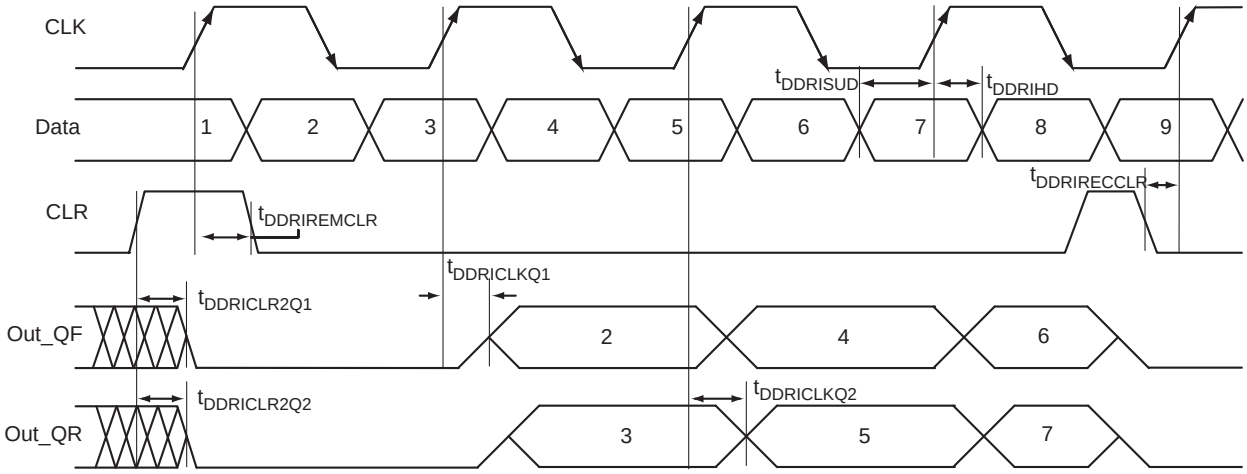


Figure 2-22 • **Input DDR Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-164 • **Input DDR Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR for Input DDR	0.48	ns
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF for Input DDR	0.65	ns
$t_{DDRISUD1}$	Data Setup for Input DDR (negedge)	0.50	ns
$t_{DDRISUD2}$	Data Setup for Input DDR (posedge)	0.40	ns
$t_{DDRIHD1}$	Data Hold for Input DDR (negedge)	0.00	ns
$t_{DDRIHD2}$	Data Hold for Input DDR (posedge)	0.00	ns
$t_{DDRICLR2Q1}$	Asynchronous Clear-to-Out Out_QR for Input DDR	0.82	ns
$t_{DDRICLR2Q2}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.98	ns
$t_{DDRIREMCLR}$	Asynchronous Clear Removal Time for Input DDR	0.00	ns
$t_{DDRIRECCLR}$	Asynchronous Clear Recovery Time for Input DDR	0.23	ns
$t_{DDRIWCLR}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.19	ns
$t_{DDRICKMPWH}$	Clock Minimum Pulse Width High for Input DDR	0.31	ns
$t_{DDRICKMPWL}$	Clock Minimum Pulse Width Low for Input DDR	0.28	ns
$F_{DDRIMAX}$	Maximum Frequency for Input DDR	250.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-190 • IGLOO CCC/PLL Specification
For IGLOO V2 Devices, 1.2 V DC Core Supply Voltage

Parameter	Min.	Typ.	Max.	Units
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}	1.5		160	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}	0.75		160	MHz
Delay Increments in Programmable Delay Blocks [1, 2]		580[3]		ps
Number of Programmable Values in Each Programmable Delay Block			32	
Serial Clock (SCLK) for Dynamic PLL[4,5]			60	ns
Input Cycle-to-Cycle Jitter (peak magnitude)			0.25	ns
Acquisition Time				
LockControl = 0			300	µs
LockControl = 1			6.0	ms
Tracking Jitter[6]				
LockControl = 0			4	ns
LockControl = 1			3	ns
Output Duty Cycle	48.5		51.5	%
Delay Range in Block: Programmable Delay 1[1,2]	2.3		20.86	ns
Delay Range in Block: Programmable Delay 2[1,2]	0.863		20.86	ns
Delay Range in Block: Fixed Delay [1, 2, 5]		5.7		ns
CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT}	Maximum Peak-to-Peak Jitter Data[7,8]			
	SSO ≥ 4[9]	SSO ≥ 8[9]	SSO ≥ 16[9]	
0.75 MHz to 50 MHz	1.20%	2.00%	3.00%	
50 MHz to 160 MHz	5.00%	7.00%	15.00%	

Notes:

1. *This delay is a function of voltage and temperature. See Table 2-6 on page 2-7 and Table 2-7 on page 2-7 for deratings.*
2. *T_J = 25°C, V_{CC} = 1.2 V*
3. *When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the Libero SoC Online Help associated with the core for more information.*
4. *Maximum value obtained for a Std. speed grade device in Worst-Case Commercial Conditions. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*
5. *The AGL030 device does not support a PLL.*
6. *Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to the PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by the period jitter parameter.*
7. *VCO output jitter is calculated as a percentage of the VCO frequency. The jitter (in ps) can be calculated by multiplying the VCO period by the per cent jitter. The VCO jitter (in ps) applies to CCC_OUT regardless of the output divider settings. For example, if the jitter on VCO is 300 ps, the jitter on CCC_OUT is also 300 ps, regardless of the output divider settings.*
8. *Measurements done with LVTTL 3.3 V, 8 mA I/O drive strength, and high slew Rate. VCC/VCCPLL = 1.14 V, VQ/PQ/TQ type of packages, 20 pF load.*
9. *SSO are outputs that are synchronous to a single clock domain and have clock-to-out times that are within ±200 ps of each other. Switching I/Os are placed outside of the PLL bank. Refer to the "Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout" section in the IGLOO FPGA Fabric User Guide.*
10. *For definitions of Type 1 and Type 2, refer to the PLL Block Diagram in the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter of the IGLOO FPGA Fabric User Guide.*

1.2 V DC Core Voltage

***Table 2-193* • RAM4K9**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.53	ns
t_{AH}	Address hold time	0.29	ns
t_{ENS}	REN WEN setup time	1.50	ns
t_{ENH}	REN, WEN hold time	0.29	ns
t_{BKS}	BLK setup time	3.05	ns
t_{BKH}	BLK hold time	0.29	ns
t_{DS}	Input data (DIN) setup time	1.33	ns
t_{DH}	Input data (DIN) hold time	0.66	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	6.61	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	5.72	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	3.38	ns
t_{C2CWWL}[1]	Address collision clk-to-clk delay for reliable write after write on same address – Applicable to Closing Edge	0.30	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address – Applicable to Opening Edge	0.89	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address – Applicable to Opening Edge	1.01	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	3.86	ns
	RESET Low to data out Low on DOUT (pipelined)	3.86	ns
$t_{REMRSTB}$	RESET removal	1.12	ns
$t_{RECRSTB}$	RESET recovery	5.93	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Embedded FlashROM Characteristics

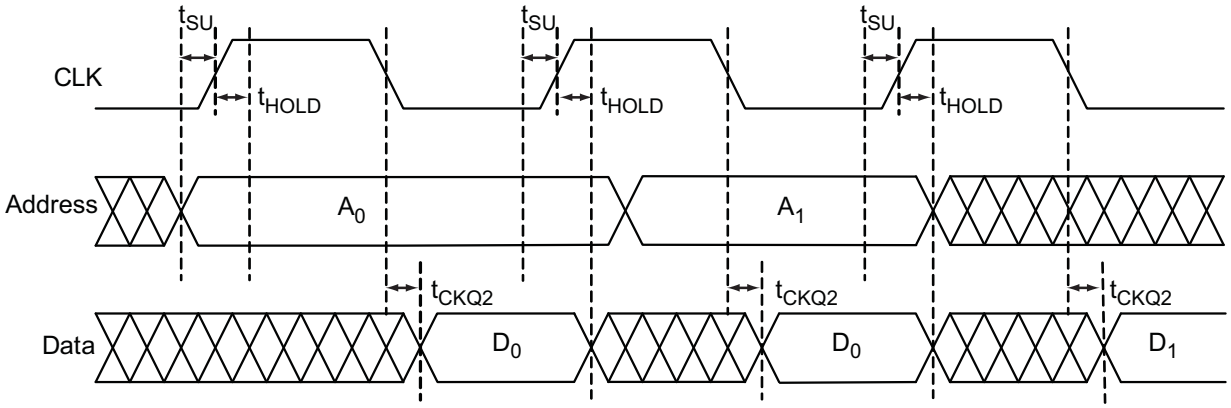


Figure 2-45 • **Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-197 • **Embedded FlashROM Access Time**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

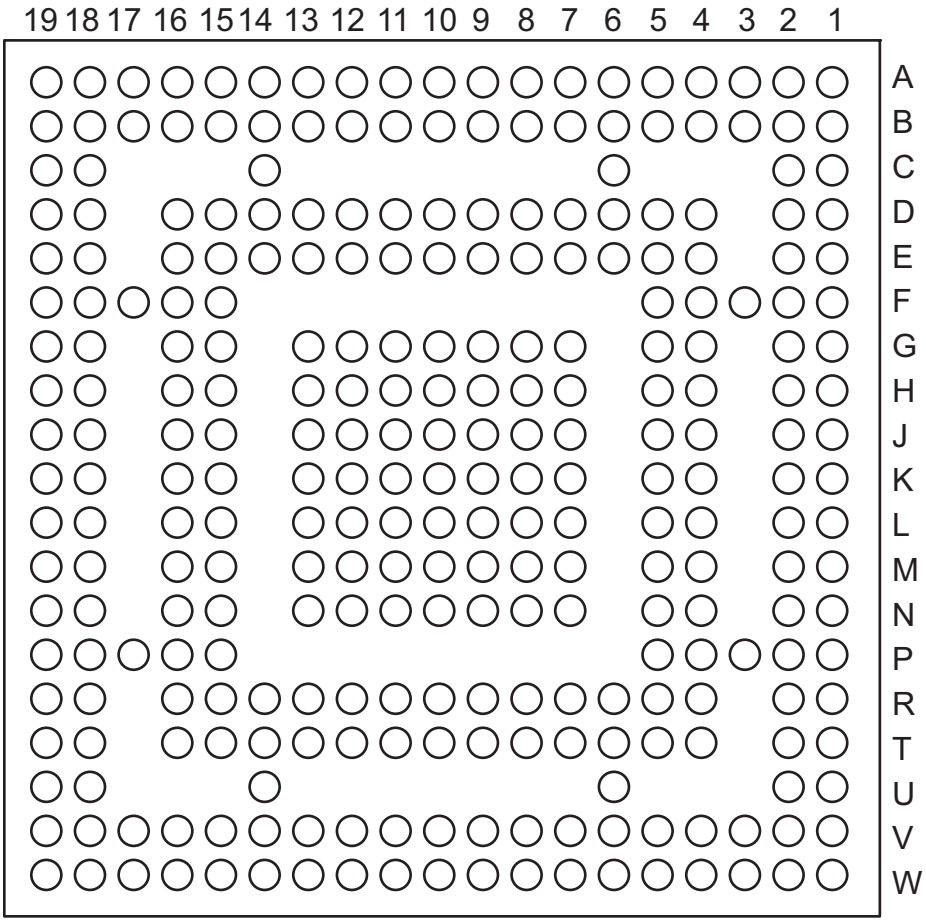
Parameter	Description	Std.	Units
t_{SU}	Address Setup Time	0.57	ns
t_{HOLD}	Address Hold Time	0.00	ns
t_{CK2Q}	Clock to Out	34.14	ns
F_{MAX}	Maximum Clock Frequency	15	MHz

1.2 V DC Core Voltage

Table 2-198 • **Embedded FlashROM Access Time**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.	Units
t_{SU}	Address Setup Time	0.59	ns
t_{HOLD}	Address Hold Time	0.00	ns
t_{CK2Q}	Clock to Out	52.90	ns
F_{MAX}	Maximum Clock Frequency	10	MHz

CS281

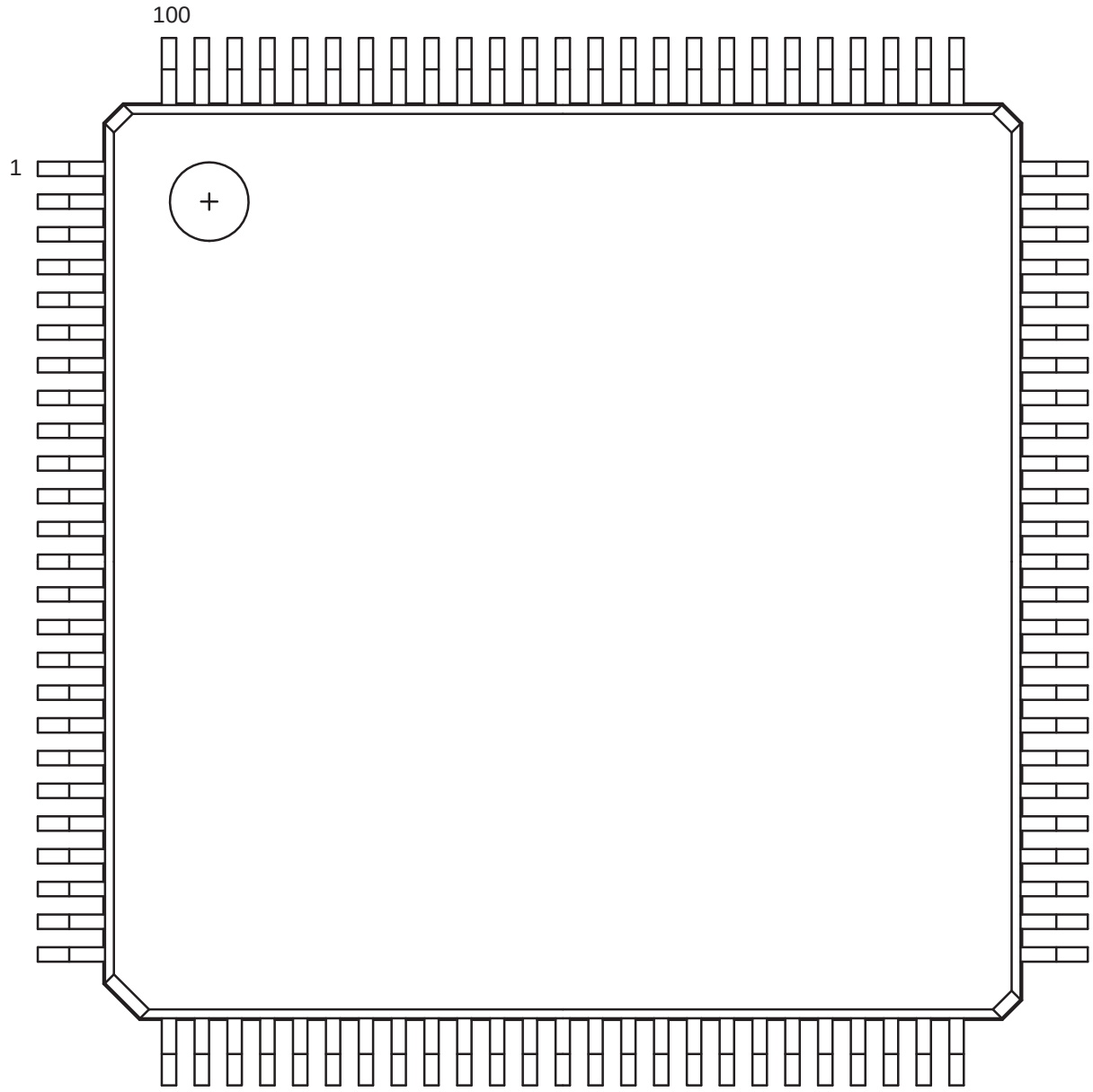


Note: This is the bottom view of the package.

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

VQ100

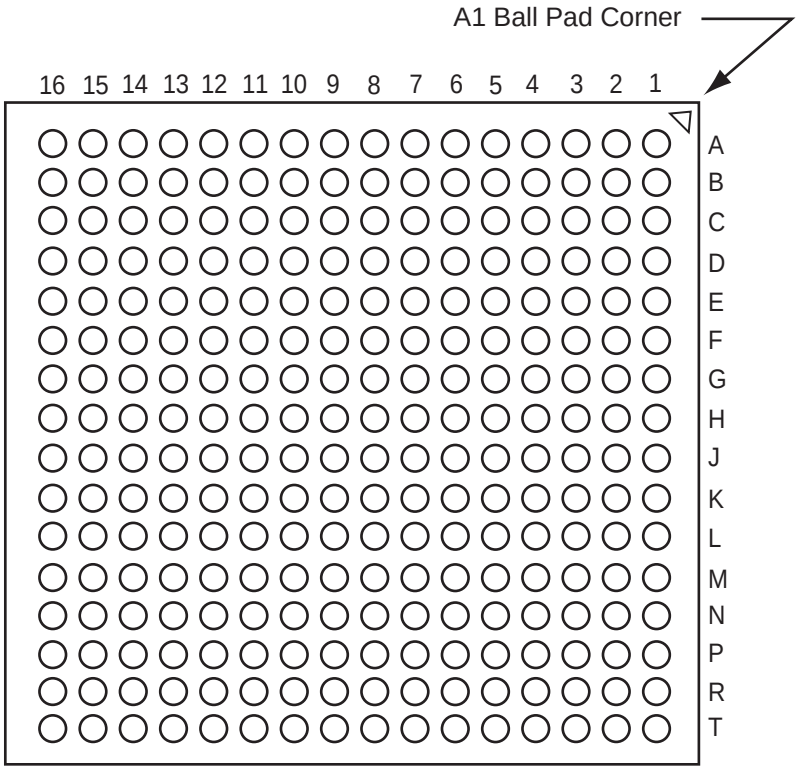


Note: This is the top view of the package.

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

FG256



Note: This is the bottom view of the package.

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

FG256	
Pin Number	**AGL1000 Function**
R5	IO168RSB2
R6	IO163RSB2
R7	IO157RSB2
R8	IO149RSB2
R9	IO143RSB2
R10	IO138RSB2
R11	IO131RSB2
R12	IO125RSB2
R13	GDB2/IO115RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO183RSB2
T3	FF/GEB2/IO186RSB2
T4	IO172RSB2
T5	IO170RSB2
T6	IO164RSB2
T7	IO158RSB2
T8	IO153RSB2
T9	IO142RSB2
T10	IO135RSB2
T11	IO130RSB2
T12	GDC2/IO116RSB2
T13	IO120RSB2
T14	GDA2/IO114RSB2
T15	TMS
T16	GND

FG484	
Pin Number	**AGL600 Function**
R9	VCCIB2
R10	VCCIB2
R11	IO117RSB2
R12	IO110RSB2
R13	VCCIB2
R14	VCCIB2
R15	VMV2
R16	IO94RSB2
R17	GDB1/IO87PPB1
R18	GDC1/IO86PDB1
R19	IO84NDB1
R20	VCC
R21	IO81NDB1
R22	IO82PDB1
T1	IO152PDB3
T2	IO152NDB3
T3	NC
T4	IO150NDB3
T5	IO147PPB3
T6	GEC1/IO146PPB3
T7	IO140RSB2
T8	GNDQ
T9	GEA2/IO143RSB2
T10	IO126RSB2
T11	IO120RSB2
T12	IO108RSB2
T13	IO103RSB2
T14	IO99RSB2
T15	GNDQ
T16	IO92RSB2
T17	VJTAG
T18	GDC0/IO86NDB1
T19	GDA1/IO88PDB1
T20	NC
T21	IO83PDB1
T22	IO82NDB1